**KEY PARAMETERS** 

 $V_{RRM}$ 

I<sub>F(AV)</sub>



DS4146-4.3

2500V

650A

7500A

**540μC** 

**5.0**μ**s** 

# **DSF8025SE**FAST RECOVERY DIODE

#### **APPLICATIONS**

- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

#### **FEATURES**

- Double side cooling.
- High surge capability.
- Low recovery charge.

#### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Reverse Voltage V <sub>RRM</sub> V	Conditions
DSF8025SE25	2500	$V_{RSM} = V_{RRM} + 100V$
DSF8025SE24	2400	NOM KKM
DSF8025SE23	2300	
DSF8025SE22	2200	
DSF8025SE21	2100	
DSF8025SE20	2000	

Lower voltage grades available.

Outline type code: E Turn to page 8 for further information.

#### **CURRENT RATINGS**

Symbol	Parameter	Conditions	Max.	Units			
Double Side Cooled							
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	650	А			
I <sub>F(RMS)</sub>	RMS value	$T_{case} = 65^{\circ}C$	1020	А			
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 65°C	785	А			
Single Side Cooled (Anode side)							
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	385	А			
I <sub>F(RMS)</sub>	RMS value	$T_{\text{case}} = 65^{\circ}\text{C}$	604	А			
I <sub>F</sub>	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	465	А			

#### DSF8025SE

#### **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; with 09/ V T = 150°C	7.5	kA
l²t	I <sup>2</sup> t for fusing	10ms half sine; with 0% $V_{RRM}$ , $T_j = 150$ °C	281 x 10 <sup>3</sup>	A <sup>2</sup> s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine: with 50% V T = 150°C	6.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 50% $V_{RRM}$ , $T_j = 150$ °C	180 x 10 <sup>3</sup>	A²s

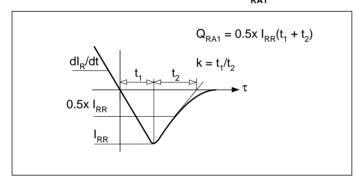
### THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance - junction to case	Double side cooled	dc	-	0.047	°C/W
		Single side cooled	Anode dc	-	0.094	°C/W
			Cathode dc	-	0.094	°C/W
В	Thermal resistance - case to heatsink	Clamping force 8.0kN with mounting compound	Double side	-	0.018	°C/W
R <sub>th(c-h)</sub>			Single side	-	0.036	°C/W
T <sub>vj</sub>	Virtual junction temperature	On-state (conducting)		-	150	°C
T <sub>stg</sub>	Storage temperature range			-55	175	°C
-	Clamping force			7.0	9.0	kN

#### **CHARACTERISTICS**

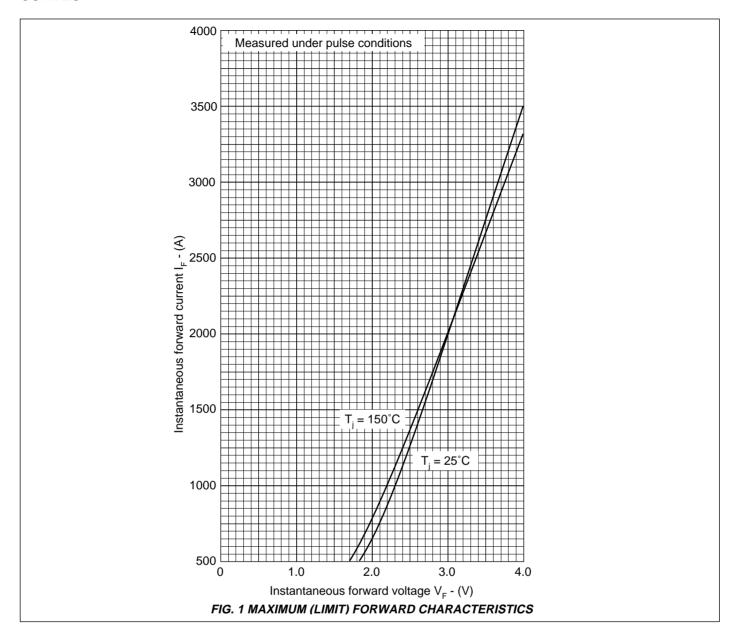
Symbol	Parameter	Conditions	Тур.	Max.	Units
V <sub>FM</sub>	Forward voltage	At 1000A peak, T <sub>case</sub> = 25°C	-	2.3	V
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 150°C	-	50	mA
t <sub>rr</sub>	Reverse recovery time		-	5.0	μs
Q <sub>RA1</sub>	Recovered charge (50% chord)	$I_{\rm F} = 1000$ A, $di_{\rm RR}/dt = 100$ A/ $\mu$ s	-	540	μС
I <sub>RM</sub>	Reverse recovery current	$T_{case} = 150^{\circ}C, V_{R} = 100V$	-	235	А
K	Soft factor		1.8	-	-
V <sub>TO</sub>	Threshold voltage	At T <sub>vj</sub> = 150°C	-	1.48	V
r <sub>T</sub>	Slope resistance	At T <sub>vj</sub> = 150°C	-	0.8	mΩ
V <sub>FRM</sub>	Forward recovery voltage	di/dt = 1000A/μs, T <sub>j</sub> = 125°C	70	-	V

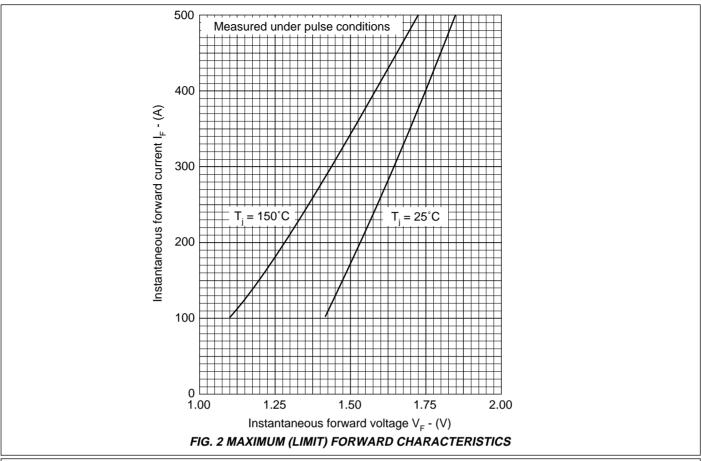
## DEFINITION OF K FACTOR AND $\boldsymbol{Q}_{\text{RA1}}$

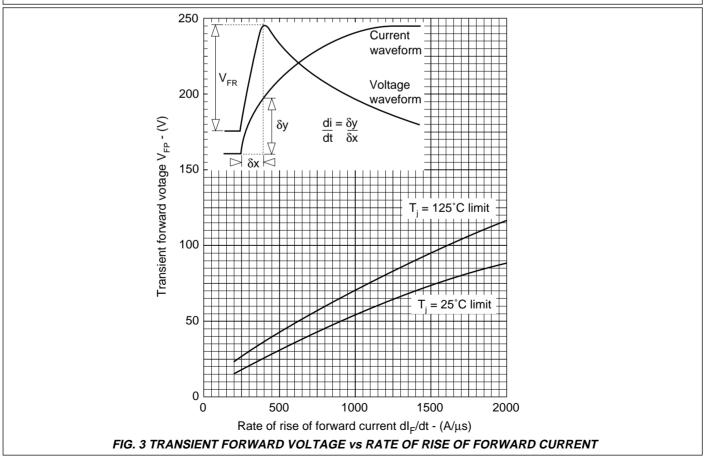


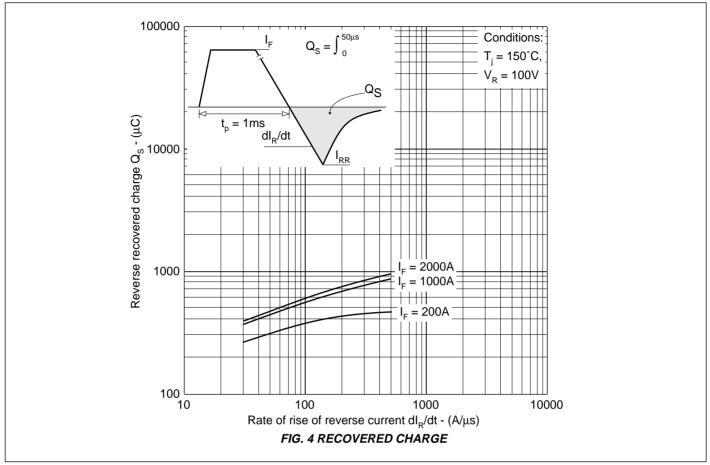
#### **DSF8025SE**

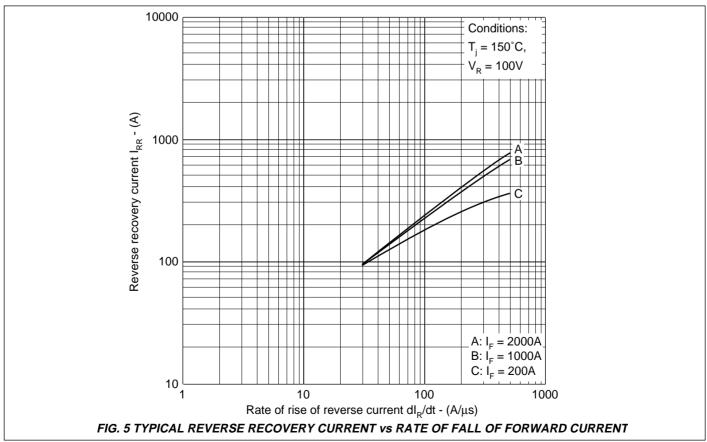
### **CURVES**

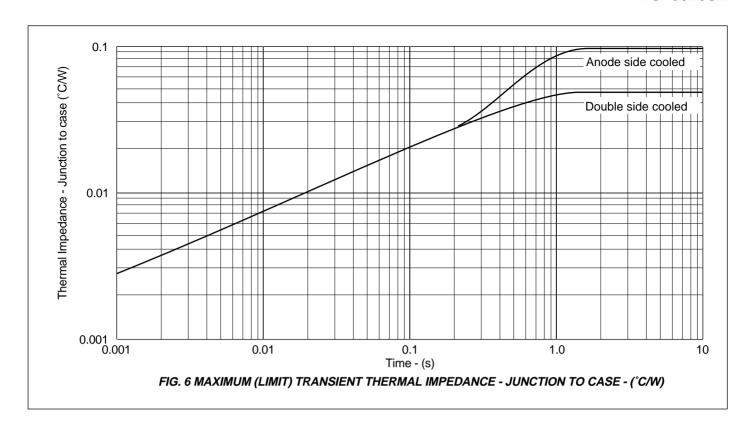






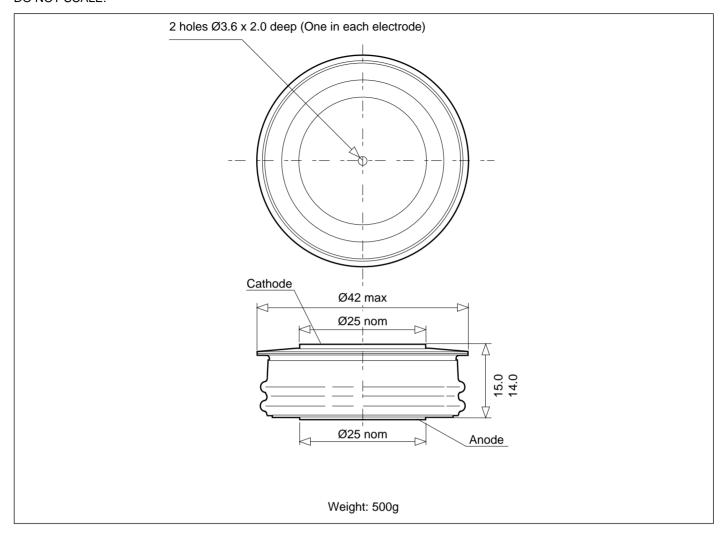






#### **PACKAGE DETAILS - CB450**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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